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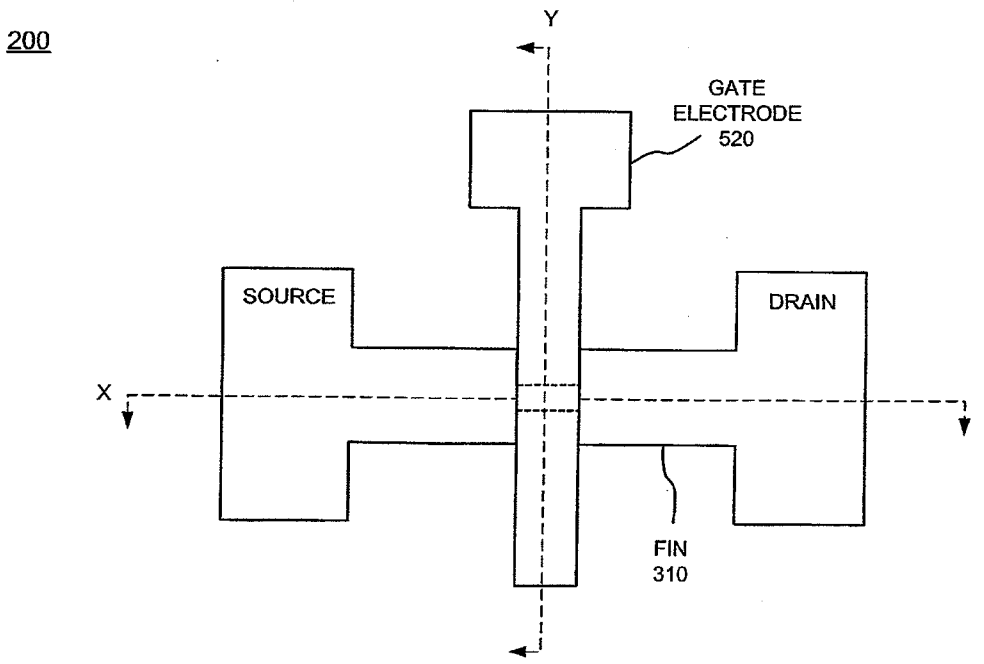
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(54) Title: SELF ALIGNED DAMASCENE GATE



(57) Abstract: A method for forming a metal-oxide semiconductor field-effect transistor (MOSFET) (200) includes patterning a fin area, a source region, and a drain region on a substrate, forming a fin (310) in the fin area, and forming a mask (320) in the fin area. The method further includes etching the mask (320) to expose a channel area (330) of the MOSFET (200), etching the fin (310) to thin a width of the fin (310) in the channel area (330), forming a gate over the fin (310), and forming contacts to the gate, the source region, and the drain region.

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